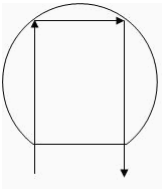


Part Number	Customer
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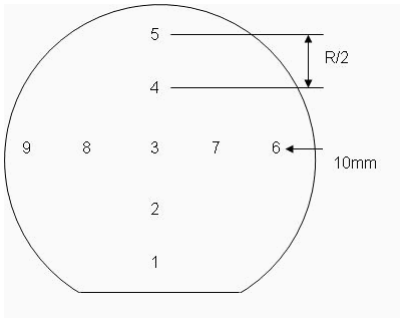
Category		Parameter	Specification	Measurement Method
Overall	Wafer	1.0 Diameter	150.00 +/- 0.30 mm	
		2.0 Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
		3.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
		4.0 Secondary Flat Orientation	semi std/none	
		5.0 Overall Thickness	501.00 +/- 17.10 µm	ADE 100%
		6.0 Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
		7.0 Bow	<80.00µm	ADE to ASTM F534, 20% Best effort not guaranteed
		8.0 Warp	<80.00µm	ADE to ASTM F657, 20% Best effort not guaranteed
		9.0 Edge Chips	0	Bright Light, 100% (note 2)
		10.0 Edge Exclusion	5mm	
Handle	Silicon	11.0 Handle Growth Method	CZ	Wafer Vendor
		12.0 Handle Orientation	{100} +/- 1 degree	Wafer Vendor
		13.0 Handle Thickness	400.00 +/- 15.00 µm	ADE, 100%
		14.0 Handle Doping Type	P	Wafer Vendor
		15.0 Handle Dopant	Boron	Wafer Vendor
		16.0 Handle Resistivity	0.1 ~ 1 Ohmcm	Wafer Vendor
		17.0 Backside Finish	Polished with laser mark and oxide.	Guaranteed by process
Buried	Oxide	18.0 Oxide Type	Thermal	
		19.0 Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
Device	Silicon	20.0 Device Growth Method	CZ	Wafer Vendor
		21.0 Device Orientation	{100} +/- 1 degree	Wafer Vendor
		22.0 Nominal Thickness	100.00 +/- 2.00 µm	ADE single point - 100%
		23.0 Device Doping Type	P	Wafer Vendor
		24.0 Device Dopant	Boron	Wafer Vendor
		25.0 Device Resistivity	0.002 - 0.01 Ohmcm	Wafer Vendor
		26.0 Voids	0	Bright Light, 100% (note 2)
		27.0 Scratches	0	Bright Light, 100% (note 2)
		28.0 Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information